

IR Laser Diode

Application

Industrial use / Biomedical

Property

Wavelength $\lambda = 980\text{nm}$

Output Power = 200mW

Package Type = $\varnothing 5.6\text{mm}$

Introduction

Egismos currently markets AlGaAs infrared laser diodes in the 780nm ~ 1550nm wavelengths range. The low operating current and high temperature of the laser diodes are achieved through using misoriented substrate and MQW (Strain compensated) active layer.

Egismos laser diodes are highly rated in a broad range of applications including, but not limited to, laser pointers, green lasers, blue laser DVD, laser barcode scanners, diode laser equipments, medical instruments and aerospace applications.

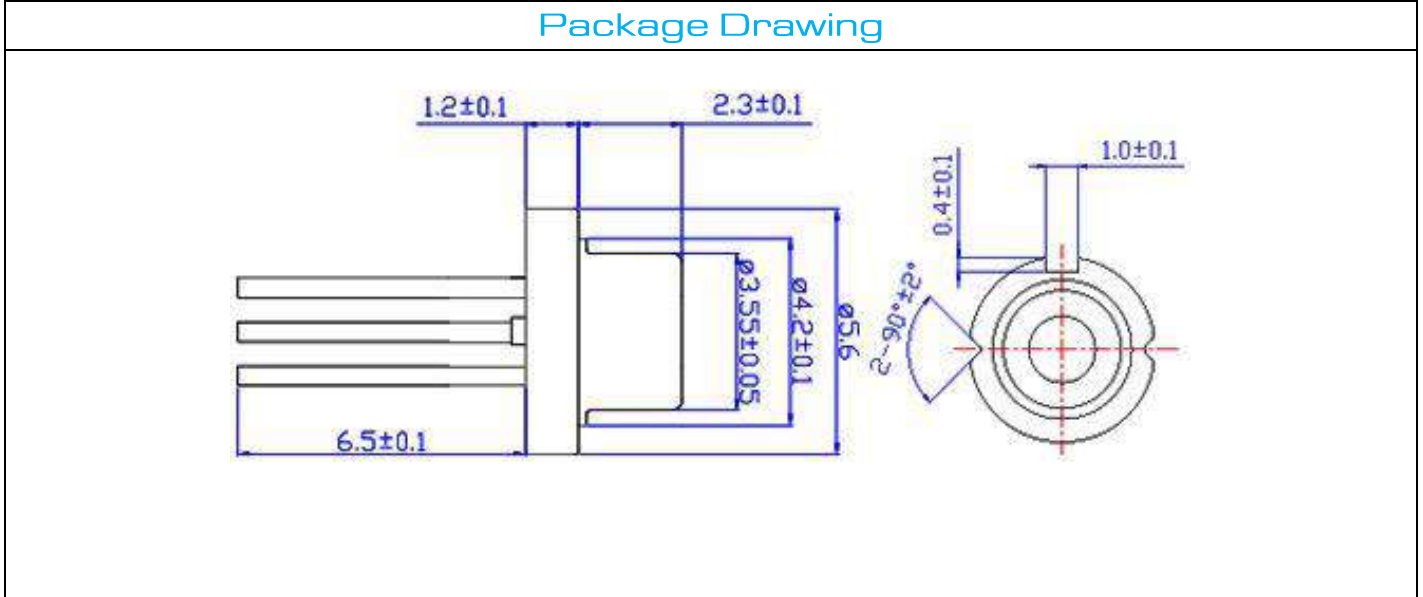
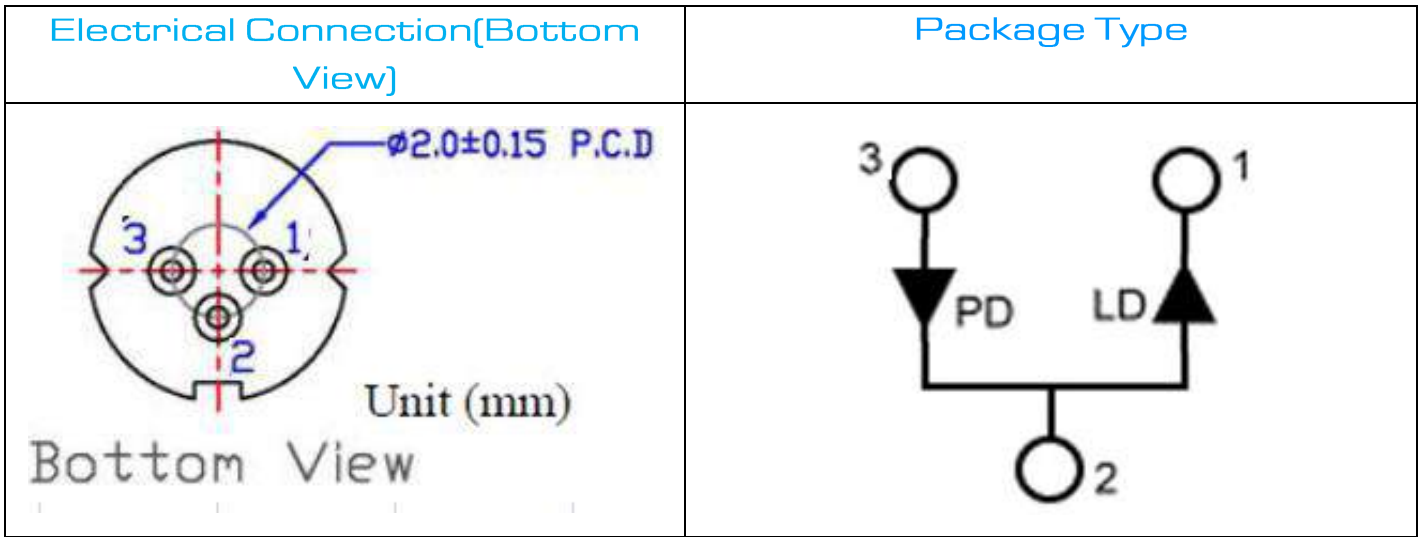


IR Laser Diode Key features

Absolute Maximum Rating at Tc=25°C			
Items	Symbols	Values	Unit
Optical Output Power	Po(CW)	200	mW
Reverse Voltage	V	2	V
Operating Temperature	To	-10~+40	°C
Storage Temperature	Ts	-10~+70	°C

Electrical and Optical Characteristics at Tc=25°C						
Item	Symbols	Min	Typ.	Max.	Unit	Condition
Optical Output Power	Po	-	-	200	mW	-
Threshold Current	Ith		60	80	mA	-
Operating Current	Iop		355	400	mA	Po=200mW
Operating Voltage	Vop	1	1.5	2.1	V	Po=200mW
Peak Wavelength	λ_p	970	980	990	nm	Po=200mW

Beam Divergence	$\theta_{//}$	-	6	-	deg	Po=200mW
	θ_{\perp}	27	30	37	deg	Po=200mW



Specifications are subject to change without notice.

